Passivation of surface-nanostructured f-SiC and porous SiC - DTU Orbit (09/11/2017)

Passivation of surface-nanostructured f-SiC and porous SiC

The further enhancement of photoluminescence from nanostructured fluorescent silicon carbide (f-SiC) and porous SiC by using atomic layer deposited (ALD) Al2O3 is studied in this paper.

General information

State: Published

Organisations: Fibers & Nonlinear Optics, Department of Photonics Engineering, Diode Lasers and LED Systems, Centre of Excellence for Silicon Photonics for Optical Communications, University of Erlangen-Nuremberg, Meijo University, Linköping University Authors: Ou, H. (Intern), Lu, W. (Intern), Ou, Y. (Intern), Jokubavicius, V. (Ekstern), Syväjärvi, M. (Ekstern), Schuh, P. (Ekstern), Wellmann, P. (Ekstern), Iwasa, Y. (Ekstern)

Number of pages: 1

Publication date: 2016

Event: Paper presented at 4th International workshop on LEDs and solar applications, Nagoya, Japan. Main Research Area: Technical/natural sciences

Bibliographical note

Invited talk at '4th International workshop on LEDs and solar applications', held at Meijo University, Nagoya, Japan, Mar.30-31, 2016 Source: PublicationPreSubmission Source-ID: 123057202 Publication: Research - peer-review > Paper – Annual report year: 2016